



STB30N65M5, STF30N65M5, STI30N65M5 STP30N65M5, STW30N65M5

N-channel 650 V, 0.125 Ω , 22 A, MDmesh™ V Power MOSFET
D²PAK, TO-220FP, I²PAK, TO-220, TO-247

Features

Order codes	V _{DSS} @ T _{JMAX}	R _{DS(on)} max.	I _D
STB30N65M5	710 V	< 0.139 Ω	22 A
STF30N65M5	710 V	< 0.139 Ω	22 A ⁽¹⁾
STI30N65M5	710 V	< 0.139 Ω	22 A
STP30N65M5	710 V	< 0.139 Ω	22 A
STW30N65M5	710 V	< 0.139 Ω	22 A

1. Limited only by maximum temperature allowed

- Worldwide best R_{DS(on)}*area
- Higher V_{DSS} rating
- Excellent switching performance
- Easy to drive
- 100% avalanche tested
- High dv/dt capability

Applications

- Switching applications

Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB30N65M5	30N65M5	D ² PAK	Tape and reel
STF30N65M5	30N65M5	TO-220FP	Tube
STI30N65M5	30N65M5	I ² PAK	Tube
STP30N65M5	30N65M5	TO-220	Tube
STW30N65M5	30N65M5	TO-247	Tube

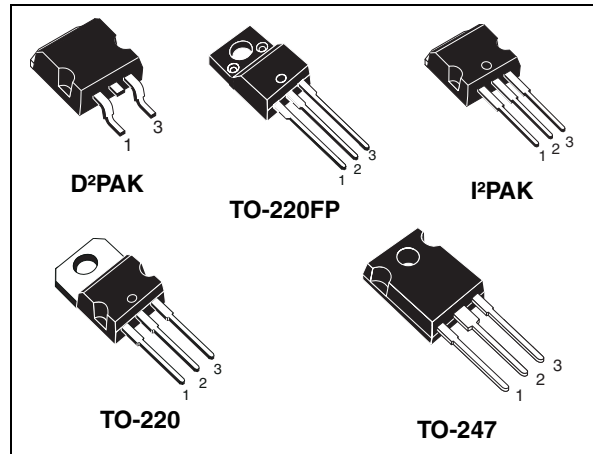
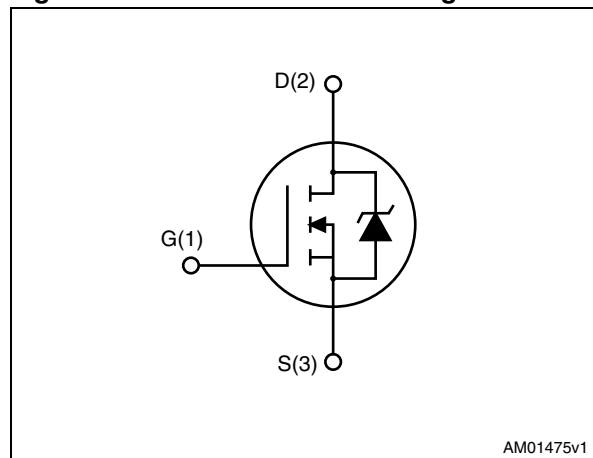


Figure 1. Internal schematic diagram



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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, D ² PAK TO-247, I ² PAK	TO-220FP	
V _{GS}	Gate-source voltage	± 25		V
I _D	Drain current (continuous) at T _C = 25 °C	22	22 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	13	13 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	88	88 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	140	30	W
I _{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T _{JMAX})	7		A
E _{AS}	Single pulse avalanche energy (starting T _j = 25°C, I _D = I _{AR} , V _{DD} = 50V)	500		mJ
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)	2500		V
T _{stg}	Storage temperature	- 55 to 150		°C
T _j	Max. operating junction temperature	150		°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- I_{SD} ≤ 21 A, di/dt = 400 A/μs, V_{Peak} < V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value					Unit
		D ² PAK	TO-220FP	I ² PAK	TO-220	TO-247	
R _{thj-case}	Thermal resistance junction-case max	0.83	3.6	0.83			°C/W
R _{thj-amb}	Thermal resistance junction-ambient max		62.5			50	°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max	30					°C/W
T _l	Maximum lead temperature for soldering purpose	300					°C

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}$		0.125	0.139	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	2880	-	pF
C_{oss}	Output capacitance			68		pF
C_{rss}	Reverse transfer capacitance			5		pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	190	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	65	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	1.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 11\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 20)	-	64	-	nC
Q_{gs}	Gate-source charge			16		nC
Q_{gd}	Gate-drain charge			25		nC

- $C_{oss\text{ eq}}$, time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
- $C_{oss\text{ eq}}$, energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(off)}$	Turn-off delay time	$V_{DD} = 400\text{ V}$, $I_D = 14\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 21)		50		ns
t_r	Rise time		-	8	-	ns
t_c	Cross time				20	ns
t_f	Fall time				10	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		22	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				88	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 22\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 22\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 21)	-	336		ns
Q_{rr}	Reverse recovery charge			6		μC
I_{RRM}	Reverse recovery current			32		A
t_{rr}	Reverse recovery time	$I_{SD} = 22\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 21)	-	395		ns
Q_{rr}	Reverse recovery charge			7		μC
I_{RRM}	Reverse recovery current			34		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK, I²PAK

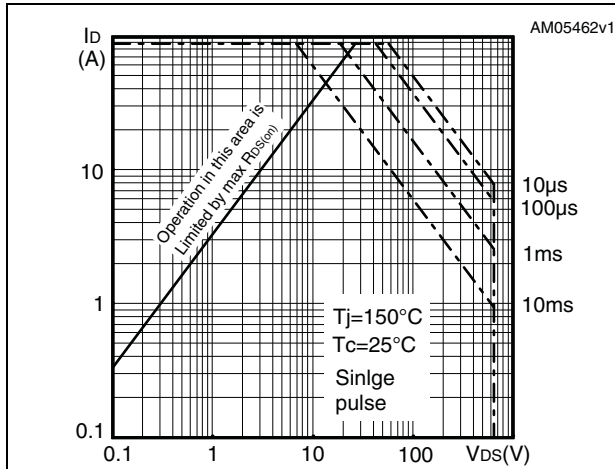


Figure 3. Thermal impedance for TO-220, D²PAK, I²PAK

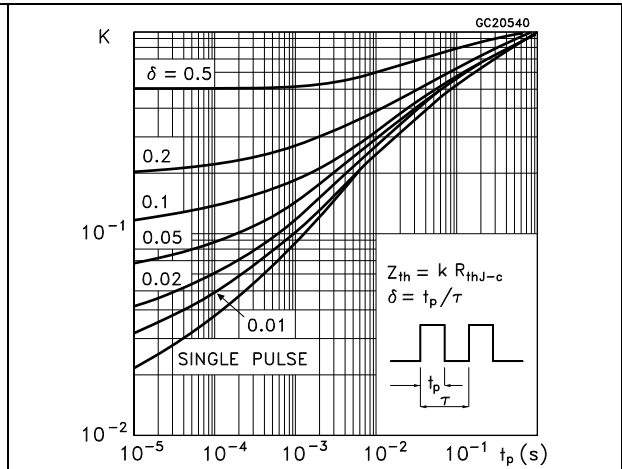


Figure 4. Safe operating area for TO-220FP

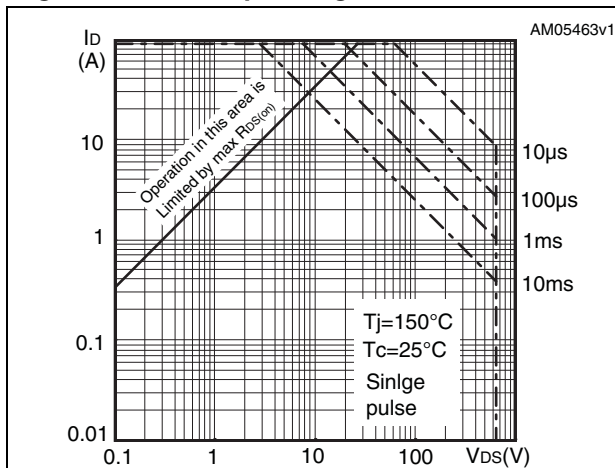


Figure 5. Thermal impedance for TO-220FP

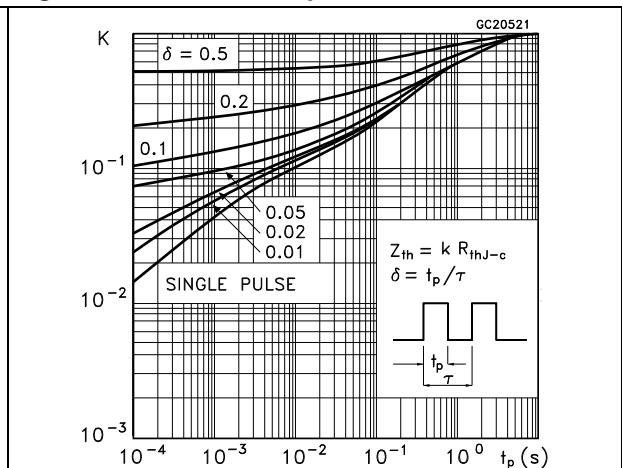


Figure 6. Safe operating area for TO-247

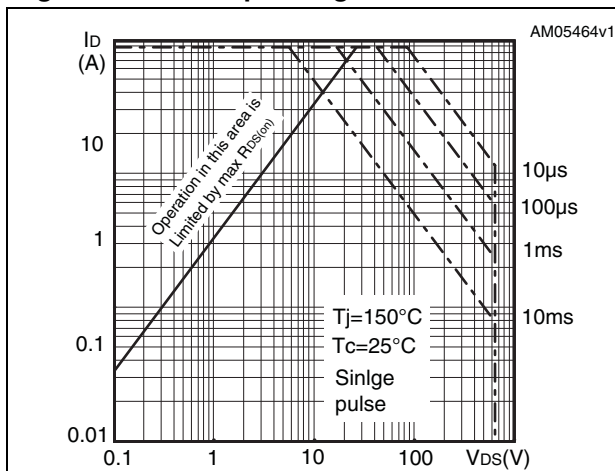


Figure 7. Thermal impedance for TO-247

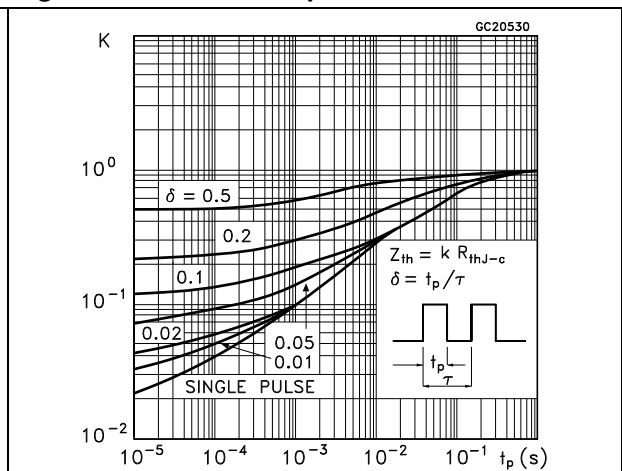


Figure 8. Output characteristics

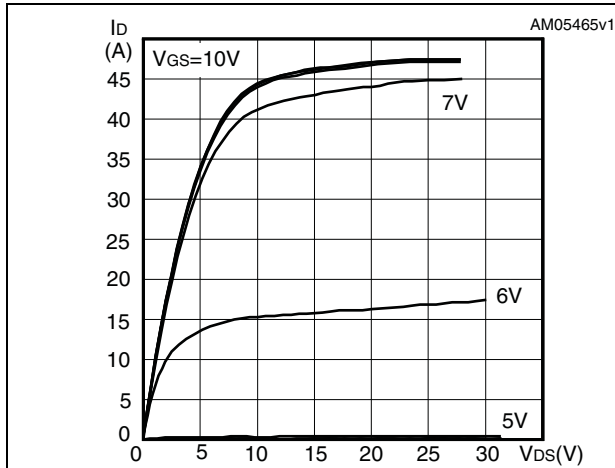


Figure 9. Transfer characteristics

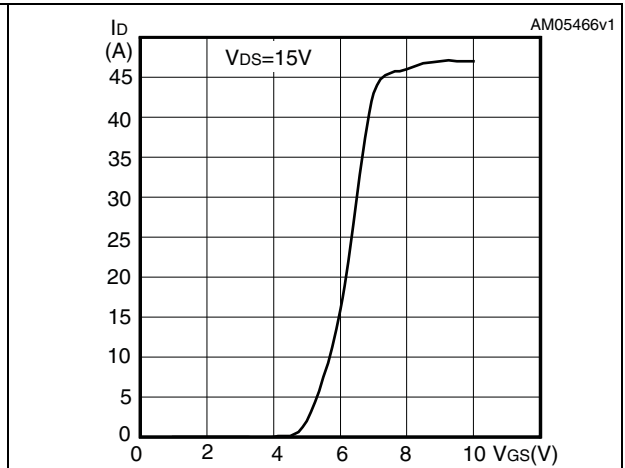


Figure 10. Gate charge vs gate-source voltage Figure 11. Static drain-source on resistance

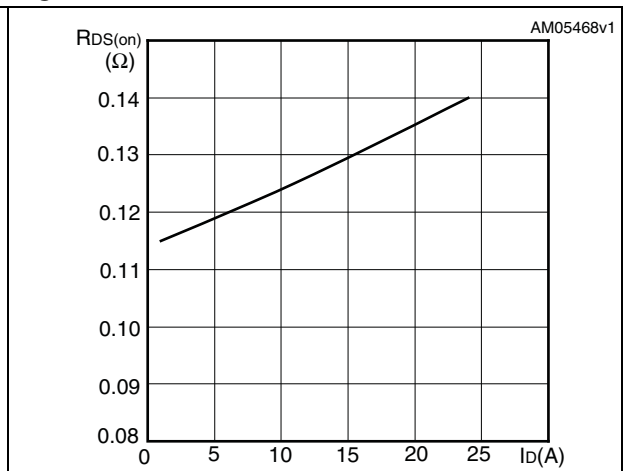
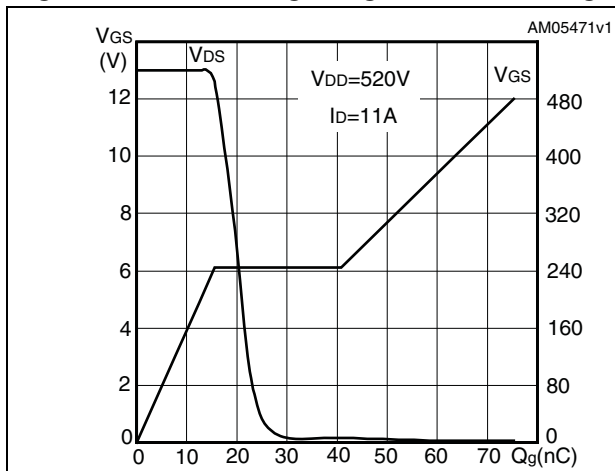


Figure 12. Capacitance variations

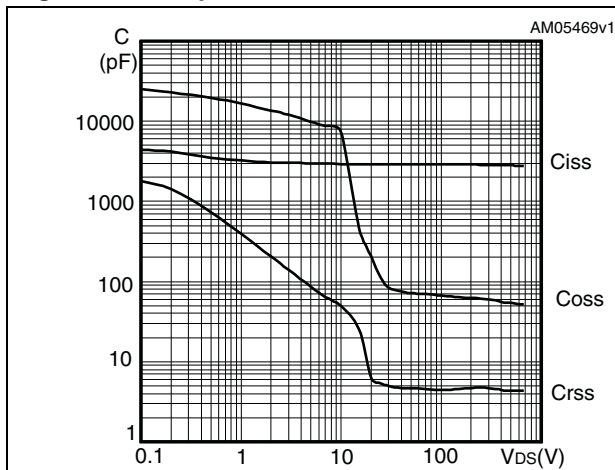


Figure 13. Output capacitance stored energy

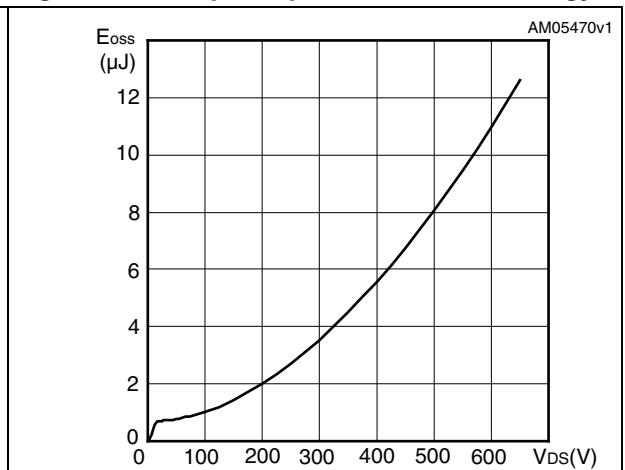


Figure 14. Normalized gate threshold voltage vs temperature

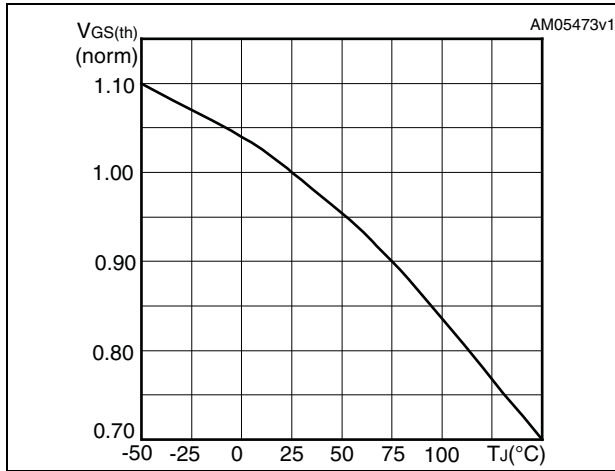


Figure 15. Normalized on resistance vs temperature

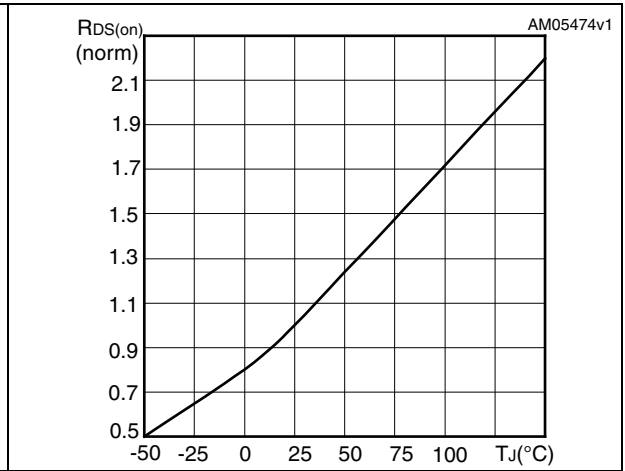


Figure 16. Source-drain diode forward characteristics

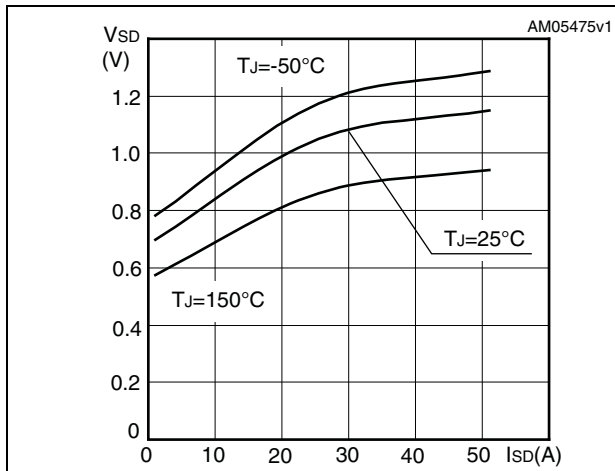


Figure 17. Normalized B_{VDSS} vs temperature

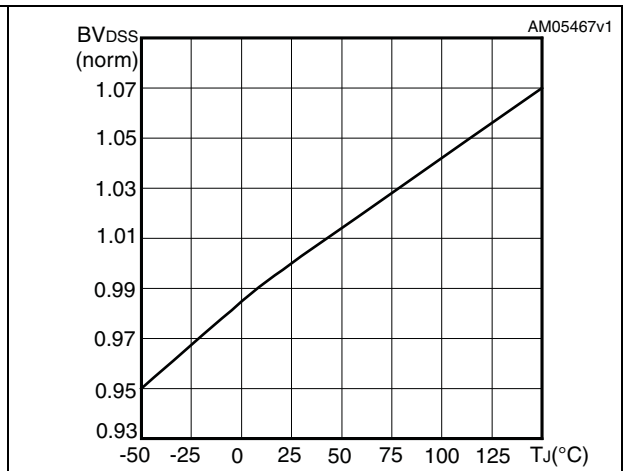
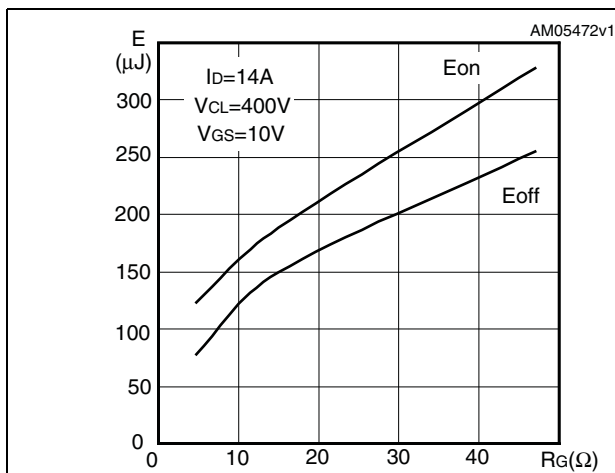


Figure 18. Switching losses vs gate resistance (1)



1. Eon including reverse recovery of a SiC diode

3 Test circuits

Figure 19. Switching times test circuit for resistive load

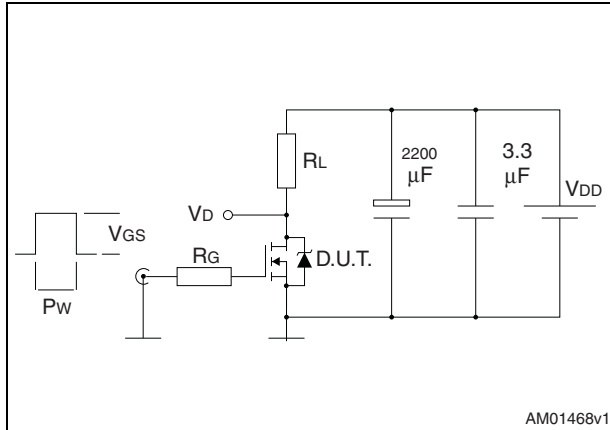


Figure 20. Gate charge test circuit

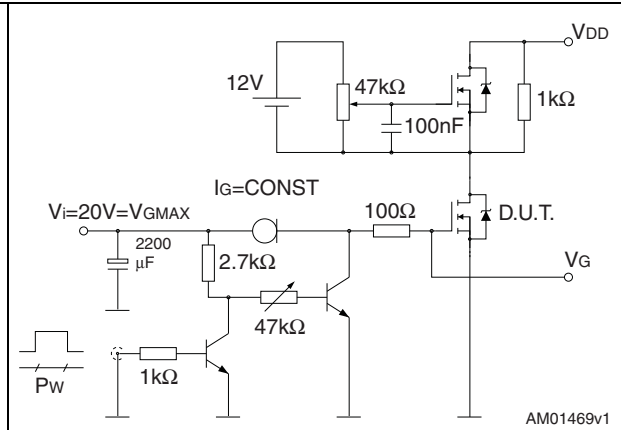


Figure 21. Test circuit for inductive load switching and diode recovery times

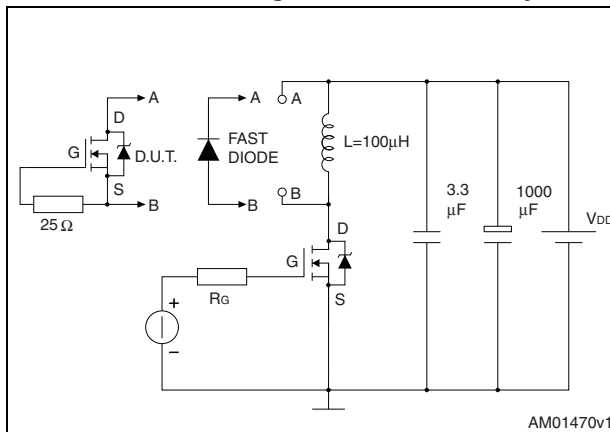


Figure 22. Unclamped inductive load test circuit

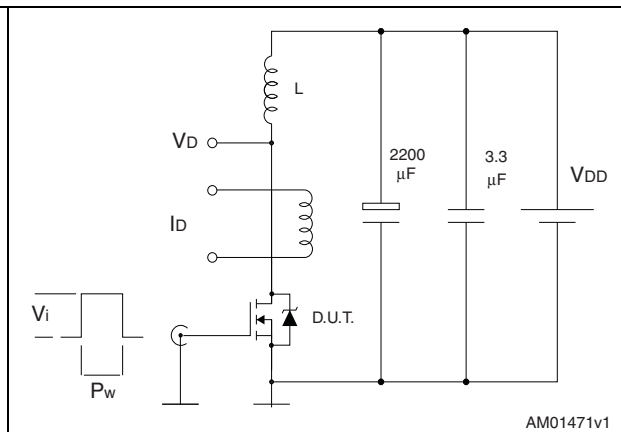


Figure 23. Unclamped inductive waveform

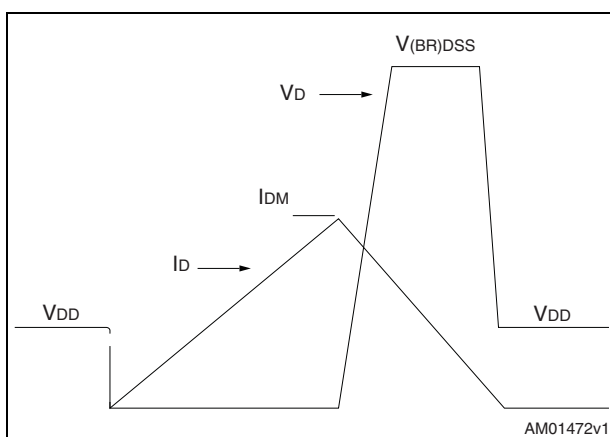
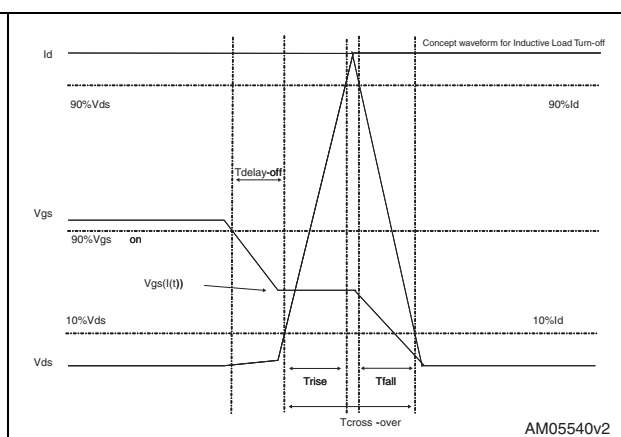


Figure 24. Switching time waveform



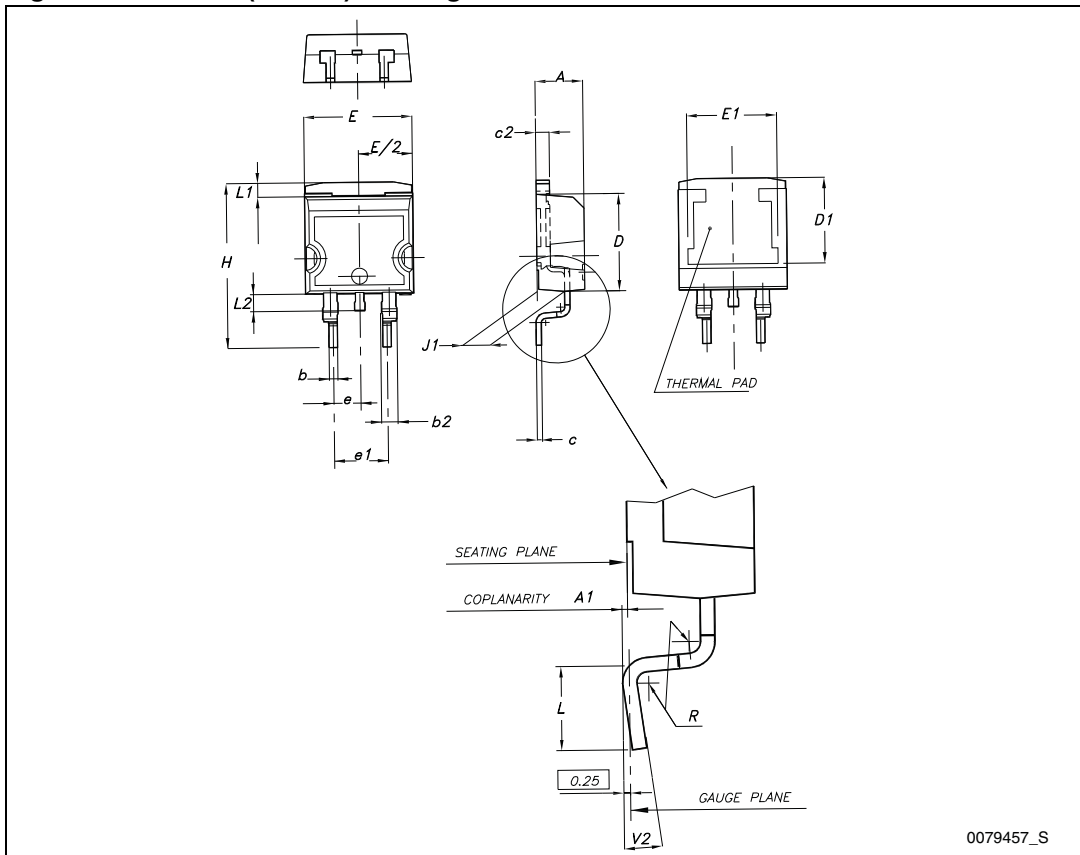
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACKm is an ST trademark.

Table 8. D²PAK (TO-263) mechanical data

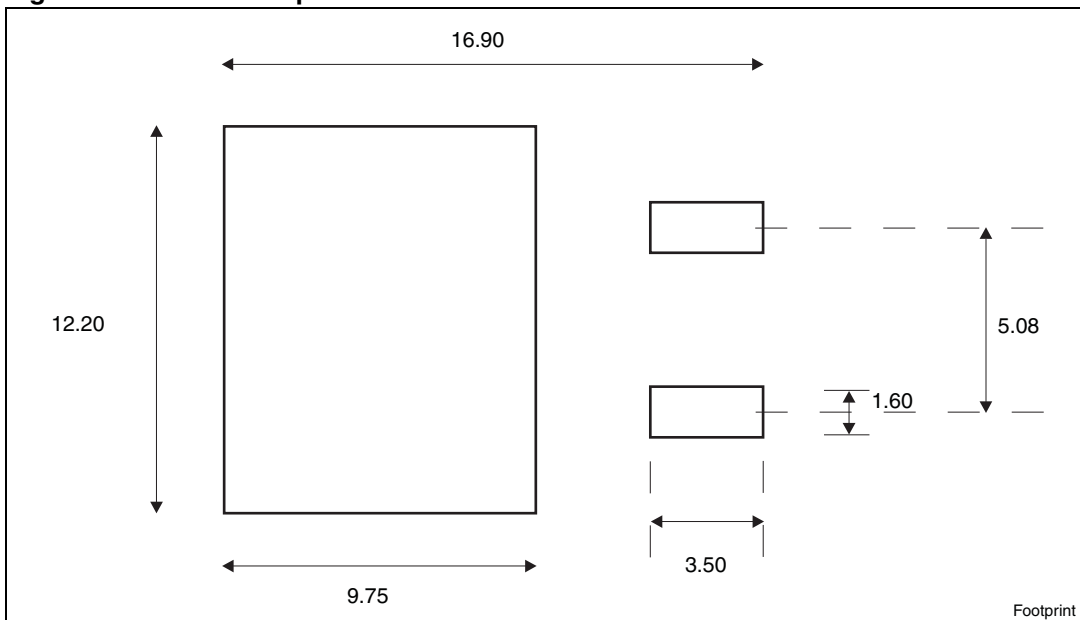
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 25. D²PAK (TO-263) drawing



0079457_S

Figure 26. D²PAK footprint^(a)



a. All dimensions are in millimeters

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 27. TO-220FP drawing

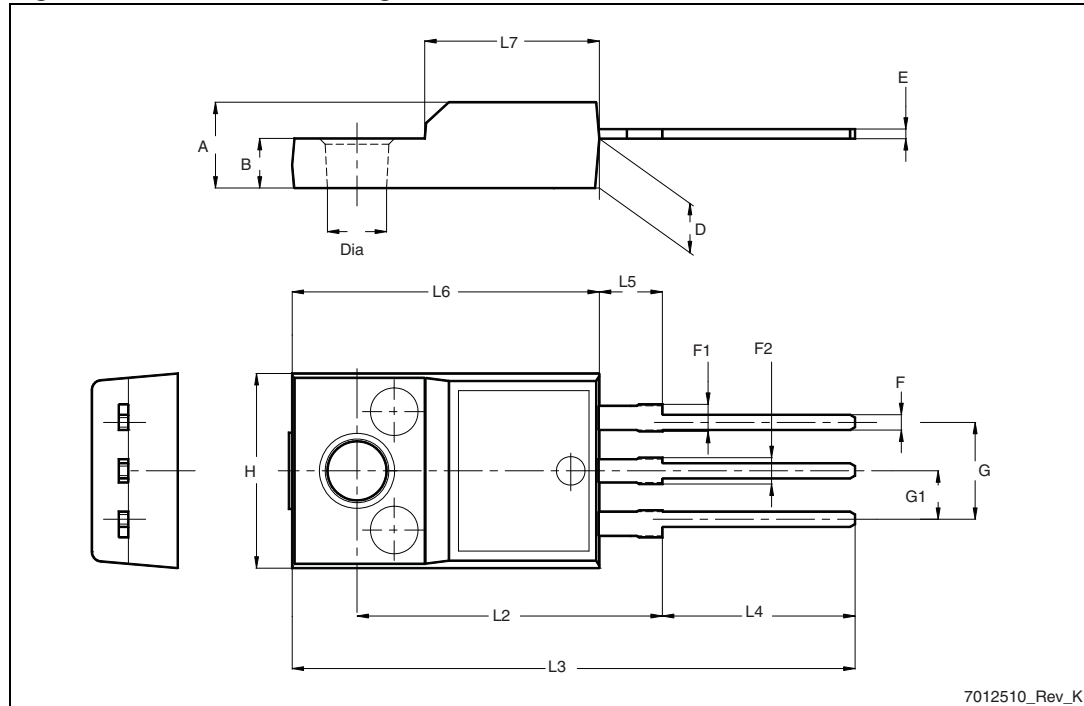


Table 10. I²PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 28. I²PAK (TO-262) drawing

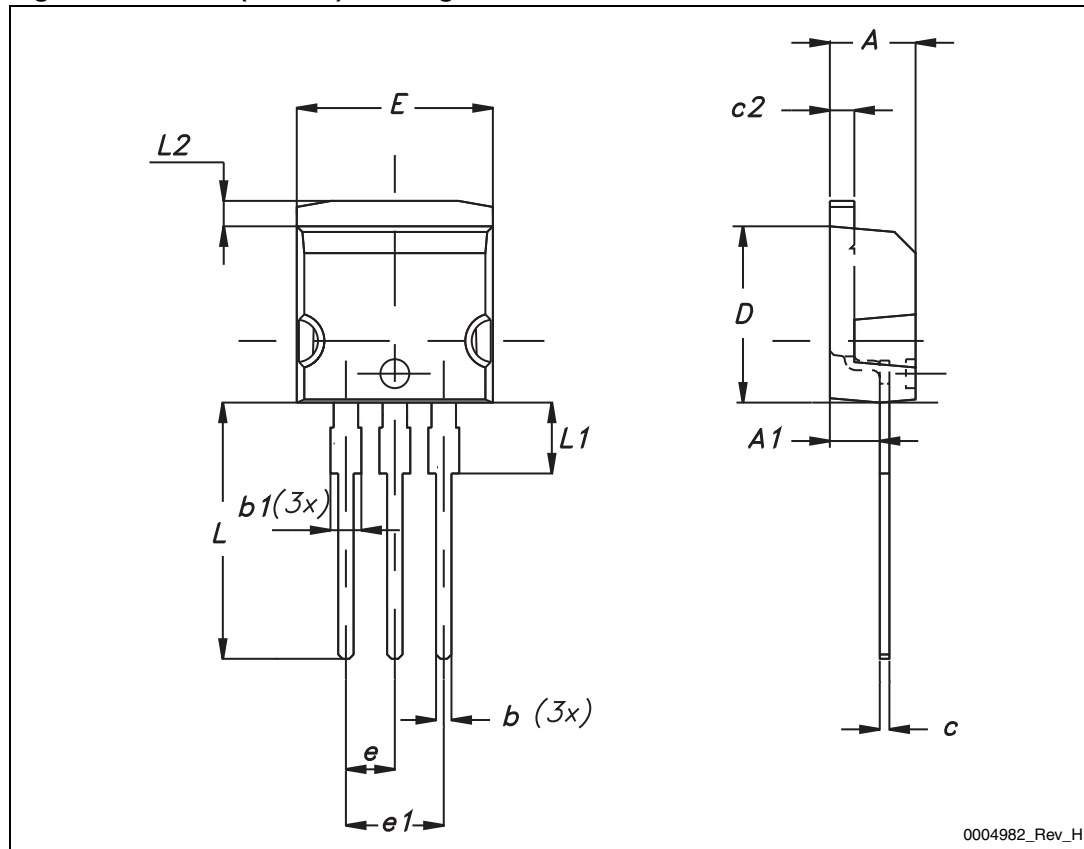


Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 29. TO-220 type A drawing

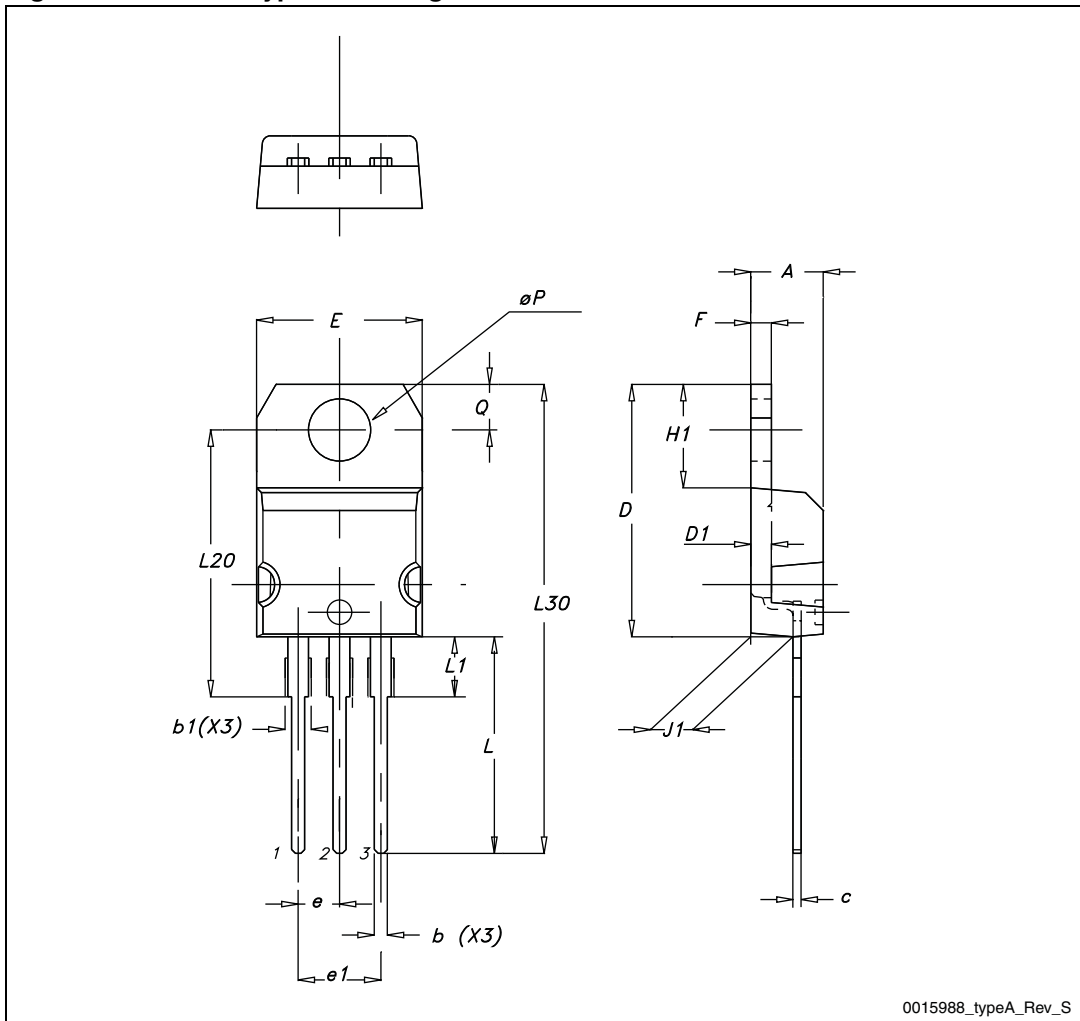
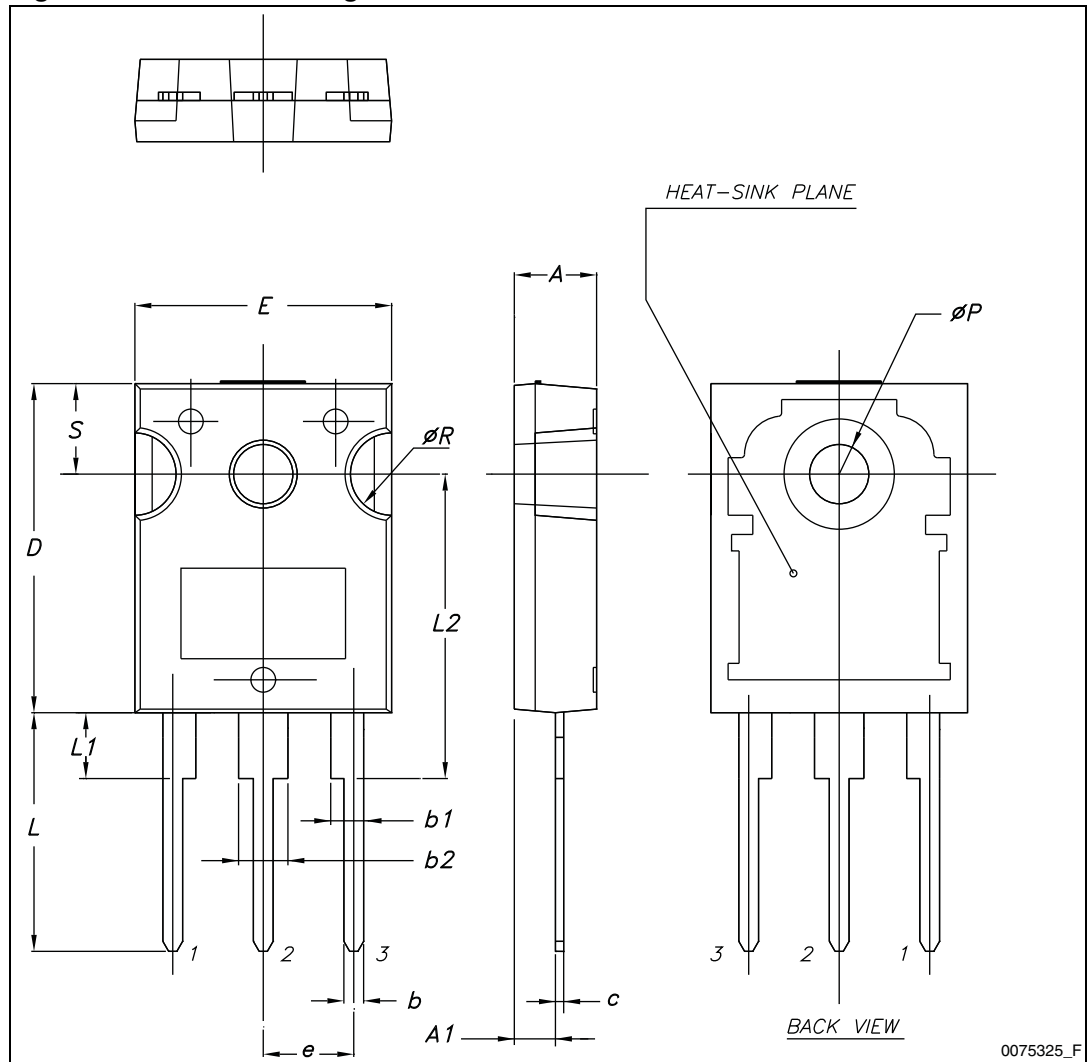


Table 12. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 30. TO-247 drawing



5 Packaging mechanical data

Table 13. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 31. Tape

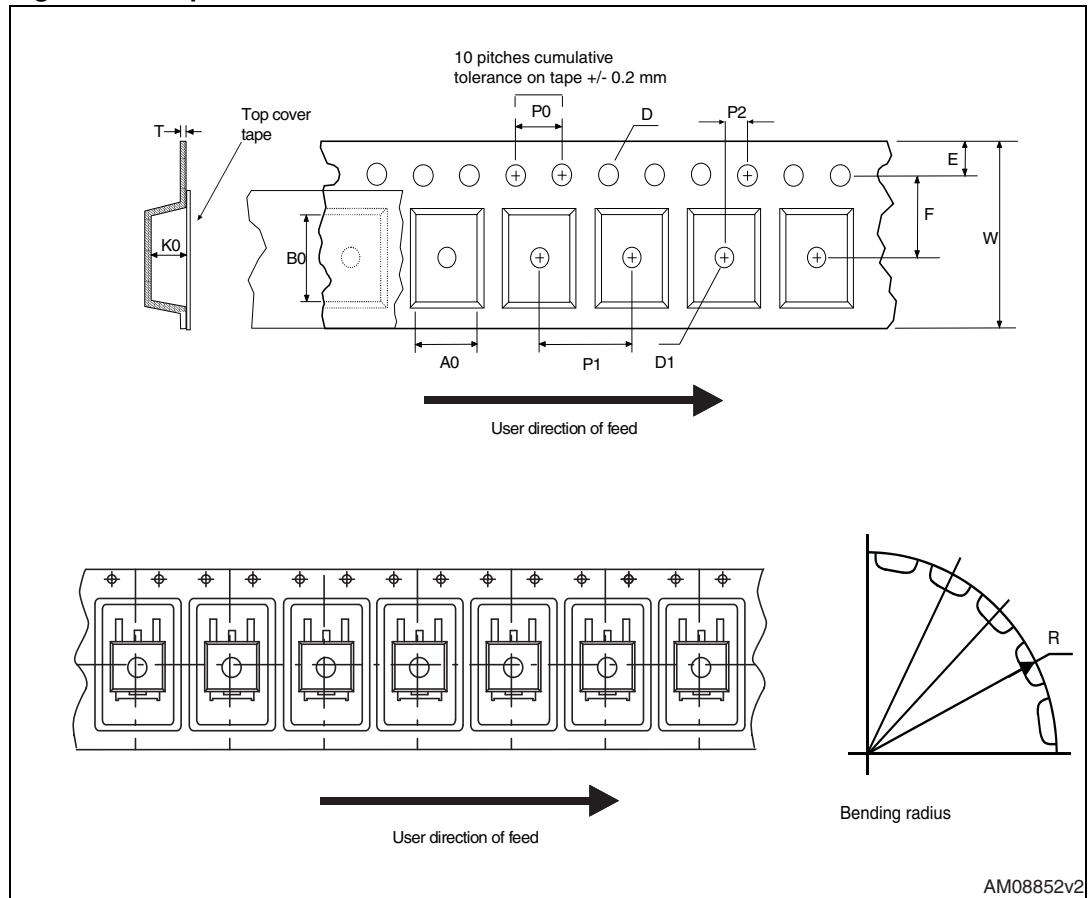
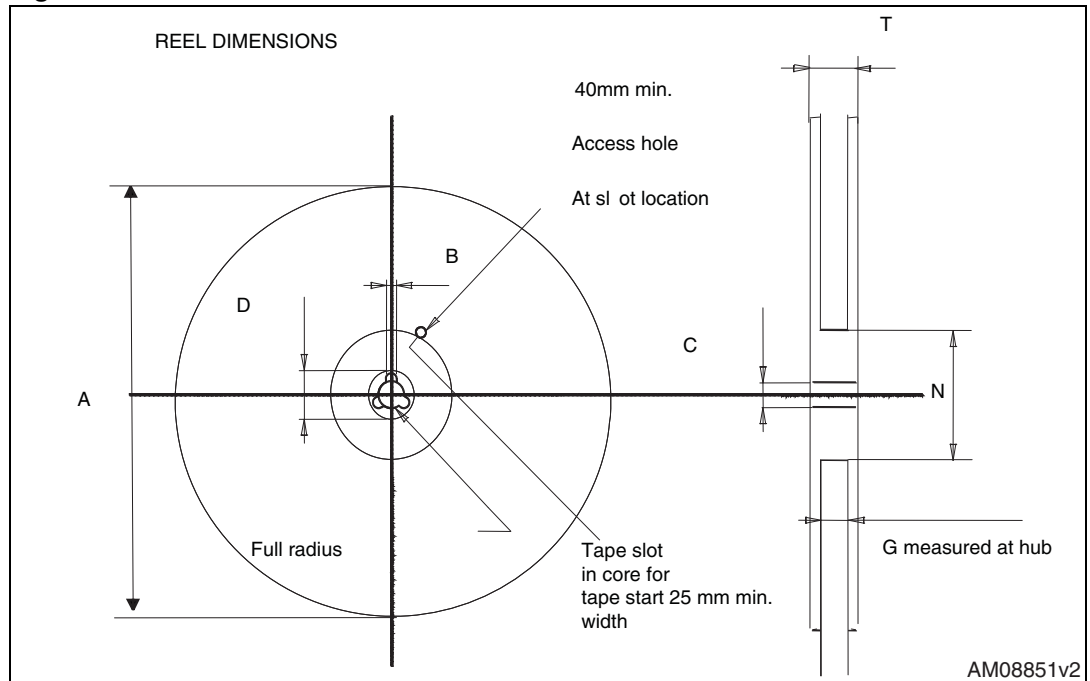


Figure 32. Reel



6 Revision history

Table 14. Document revision history

Date	Revision	Changes
16-Jan-2009	1	First release
21-Sep-2009	2	Document status promoted from preliminary data to datasheet.
22-Sep-2011	3	<p>$C_{o(er)}$ and $C_{o(tr)}$ values changed in Table 5: Dynamic Table 6: Switching times parameters updates Figure 24: Switching time waveform has been corrected Minor text changes Section 4: Package mechanical data has been modified. Added:</p> <ul style="list-style-type: none"> – Table 8: D²PAK (TO-263) mechanical data, Figure 25: D²PAK (TO-263) drawing and Figure 26: D²PAK footprint; – Table 9: TO-220FP mechanical data, and Figure 27: TO-220FP drawing; – Table 10: I²PAK (TO-262) mechanical data, and Figure 28: I²PAK (TO-262) drawing; – Table 11: TO-220 type A mechanical data, and Figure 29: TO-220 type A drawing; – Table 12: TO-247 mechanical data, and Figure 30: TO-247 drawing; <p>Section 5: Packaging mechanical data has been modified. Added:</p> <ul style="list-style-type: none"> – Table 13: D²PAK (TO-263) tape and reel mechanical data, Figure 31: Tape and Figure 32: Reel;

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